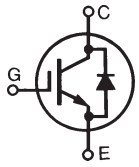
IXYS

1200V XPT™ IGBT GenX3™ w/ Diode

IXYR50N120C3D1

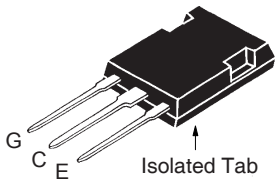
V_{CES} = 1200V
I_{C90} = 32A
$V_{CE(sat)}$ ≤ 3.5V
$t_{fi(typ)}$ = 43ns

(Electrically Isolated Tab)



High-Speed IGBT
for 20-50 kHz Switching

ISOPLUS247™



G = Gate C = Collector
E = Emitter

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	1200	V
V_{CGR}	T_J = 25°C to 150°C, R_{GE} = 1MΩ	1200	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C (Chip Capability)	56	A
I_{C90}	T_C = 90°C	32	A
I_{F110}	T_C = 110°C	18	A
I_{CM}	T_C = 25°C, 1ms	210	A
SSOA (RBSOA)	V_{GE} = 15V, T_{VJ} = 150°C, R_G = 5Ω Clamped Inductive Load	I_{CM} = 100 @$V_{CE} \leq V_{CES}$	A
P_C	T_C = 25°C	290	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
V_{ISOL}	50/60 Hz, 1 Minute	2500	V~
F_C	Mounting Force	20..120/4.5..27	N/lb.
Weight		5	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{CES}	I_C = 250μA, V_{GE} = 0V	1200			V
$V_{GE(th)}$	I_C = 250μA, V_{CE} = V_{GE}	3.0		5.0	V
I_{CES}	V_{CE} = V_{CES}, V_{GE} = 0V			50	μA
	T_J = 125°C			500	μA
I_{GES}	V_{CE} = 0V, V_{GE} = ±20V			±100	nA
$V_{CE(sat)}$	I_C = 50A, V_{GE} = 15V, Note 1			3.5	V
	T_J = 150°C		4.2		V

Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 2500V~ Electrical Isolation
- Optimized for Low Switching Losses
- Square RBSOA
- Positive Thermal Coefficient of Vce(sat)
- Anti-Parallel Ultra Fast Diode
- High Current Handling Capability
- International Standard Package

Advantages

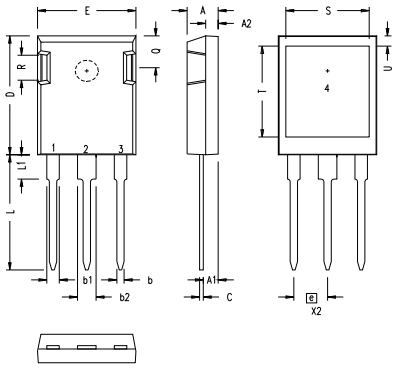
- High Power Density
- Low Gate Drive Requirement

Applications

- High Frequency Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	I_C = 50A, V_{CE} = 10V, Note 1	20	32		S
C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		3100		pF
C_{oes}			230		pF
C_{res}			66		pF
$Q_{g(on)}$	I_C = 50A, V_{GE} = 15V, V_{CE} = 0.5 • V_{CES}		142		nC
Q_{ge}			23		nC
Q_{gc}			60		nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		28		ns
t_{ri}	I_C = 50A, V_{GE} = 15V		62		ns
E_{on}	V_{CE} = 0.5 • V_{CES}, R_G = 5Ω		3.0		mJ
$t_{d(off)}$	Note 2		133		ns
t_{fi}			43		ns
E_{off}			1.0	1.7	mJ
$t_{d(on)}$	**Inductive load, T_J = 150°C**		28		ns
t_{ri}	I_C = 50A, V_{GE} = 15V		68		ns
E_{on}	V_{CE} = 0.5 • V_{CES}, R_G = 5Ω		6.0		mJ
$t_{d(off)}$	Note 2		160		ns
t_{fi}			60		ns
E_{off}			1.4		mJ
R_{thJC}				0.43	°C/W
R_{thCS}			0.15		°C/W

ISOPLUS247 (IXYR) Outline



SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.084	1.91	2.13
b2	.115	.123	2.92	3.12
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.520	.540	13.21	13.72
T	.620	.640	15.75	16.26
U	.065	.080	1.65	2.03

1 - Gate
2,4 - Collector
3 - Emiiter

Reverse Diode (FRED)

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)		Characteristic Value Min.	Typ.	Max.	
V_F	I_F = 30A,V_{GE} = 0V, Note 1				3.00	V
		T_J = 150°C		1.75		V
I_{RM}	I_F = 30A,V_{GE} = 0V, -di_F/dt = 100A/µs,	T_J = 100°C			9	A
t_{rr}	V_R = 600V	T_J = 100°C		195		ns
R_{thJC}					1.10	°C/W

Notes:

1. Pulse test, t ≤ 300µs, duty cycle, d ≤ 2%.
2. Switching times & energy losses may increase for higher V_{CE}(clamp), T_J or R_G.

Fig. 1. Output Characteristics @ T_J = 25ºC

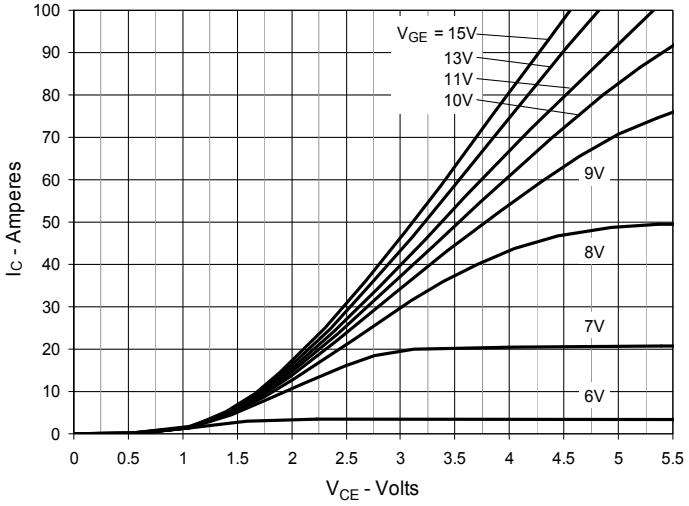


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

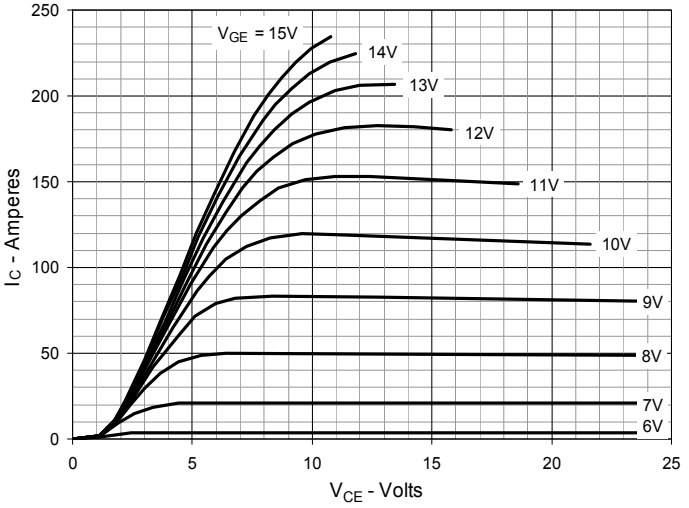


Fig. 3. Output Characteristics @ T_J = 150ºC

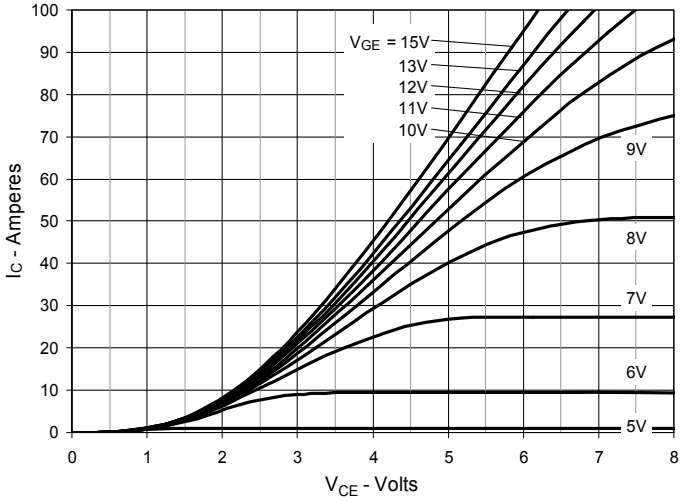


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

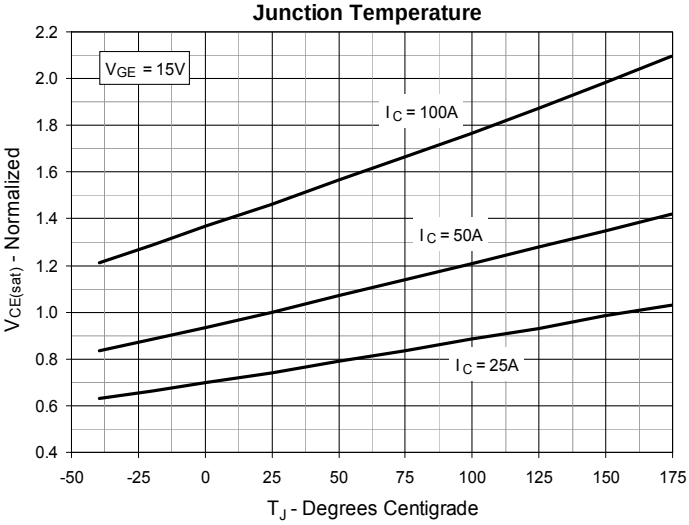


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

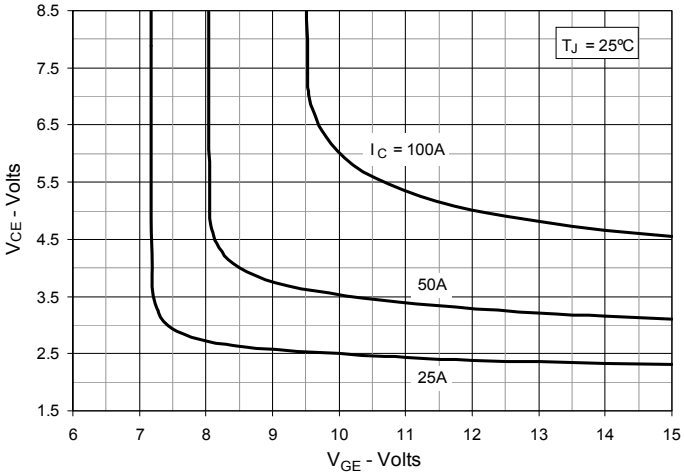


Fig. 6. Input Admittance

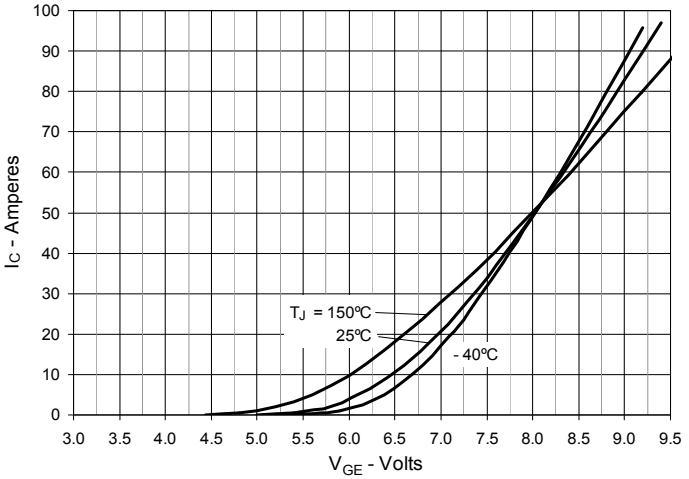


Fig. 7. Transconductance

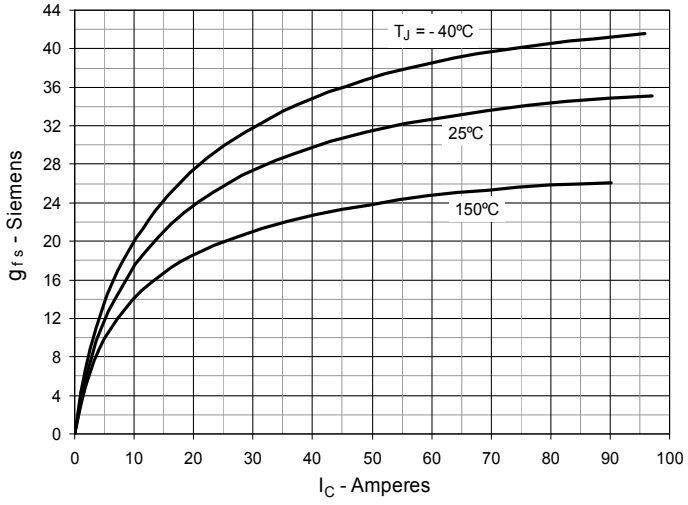


Fig. 8. Gate Charge

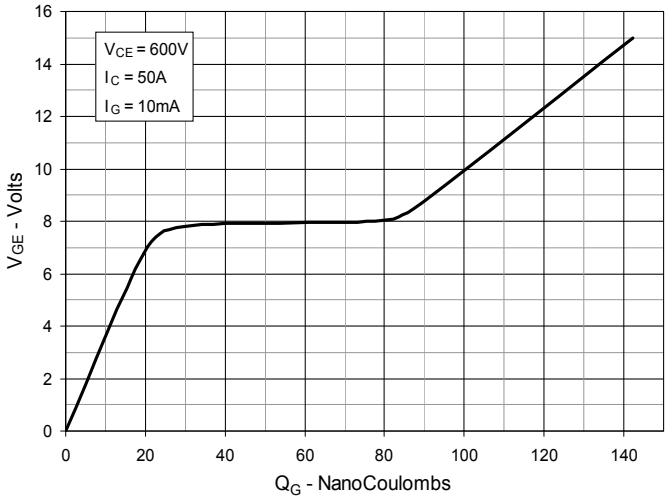


Fig. 9. Capacitance

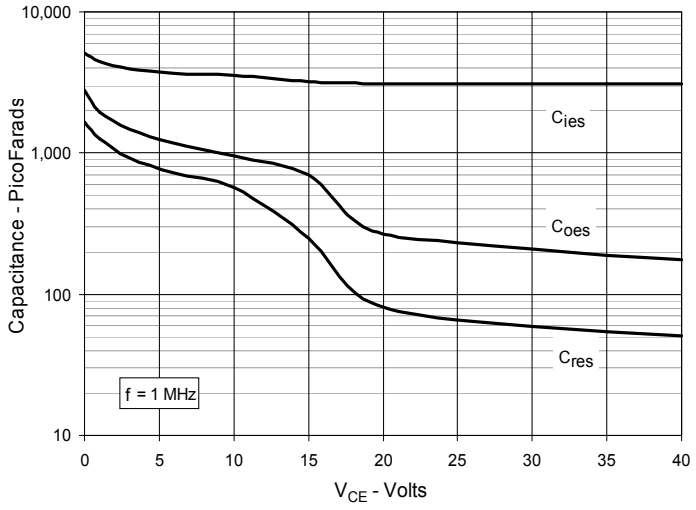


Fig. 10. Reverse-Bias Safe Operating Area

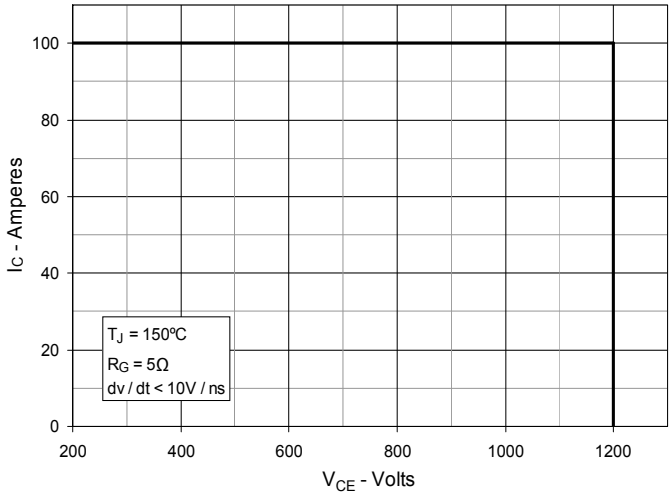


Fig. 11. Maximum Transient Thermal Impedance

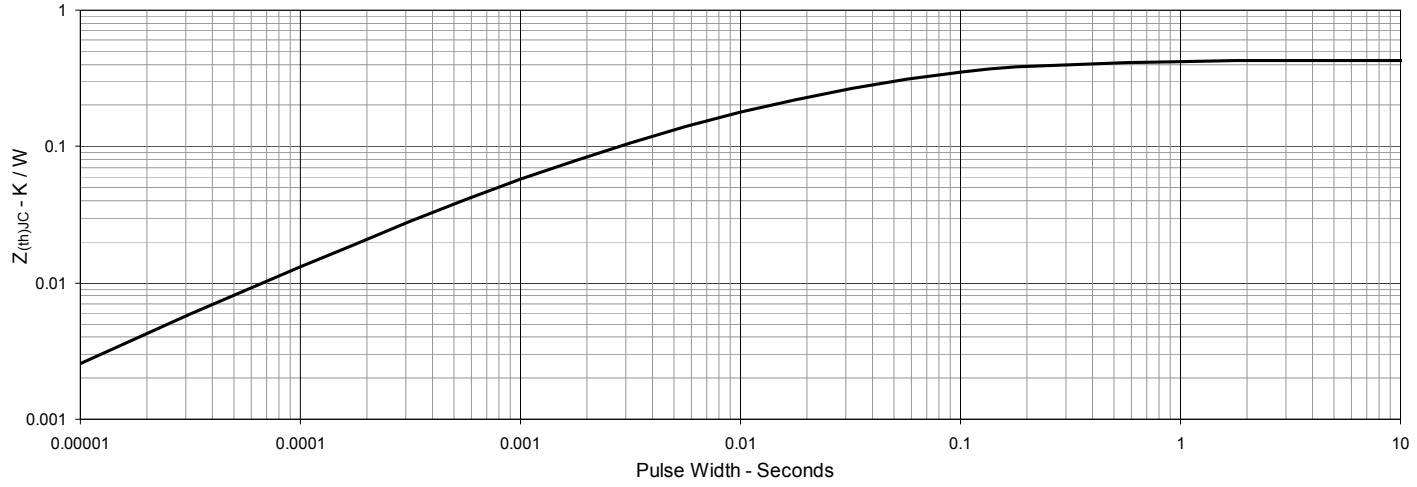


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

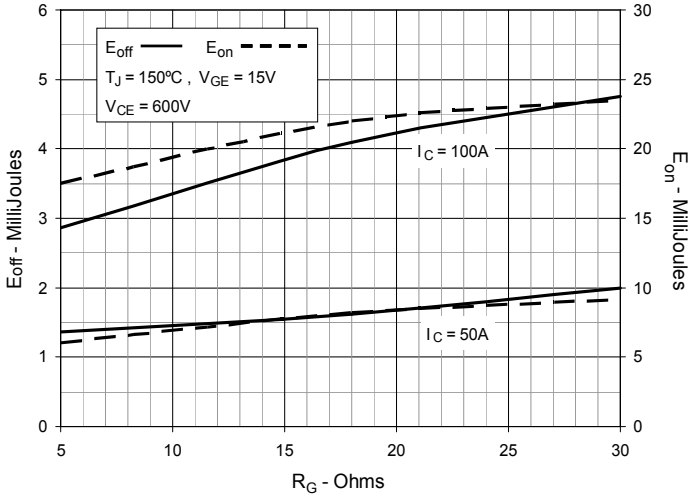


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

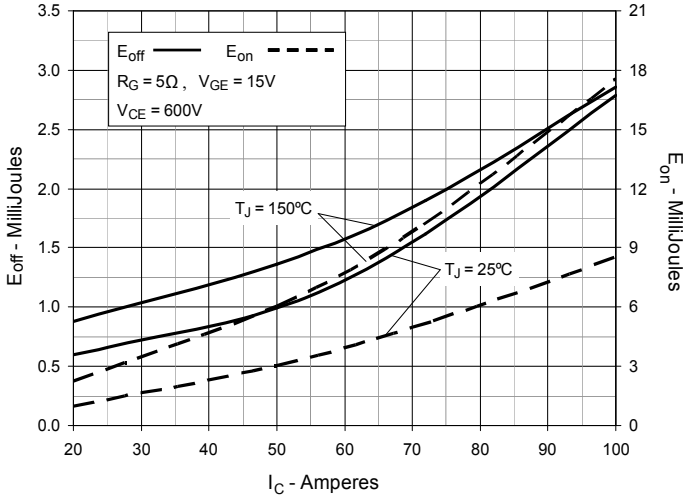


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

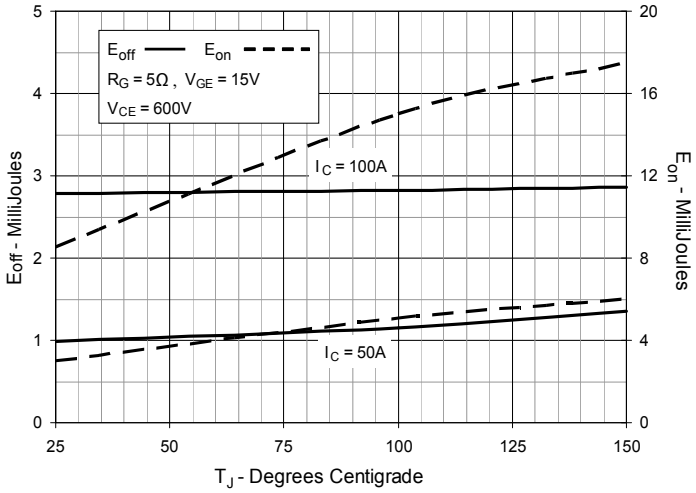


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

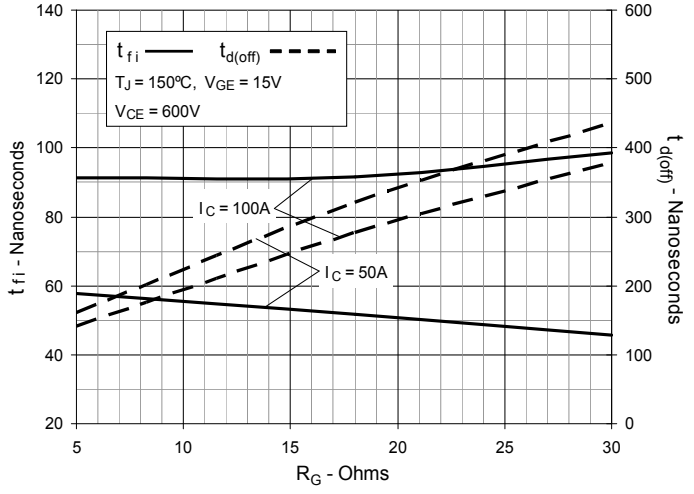


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

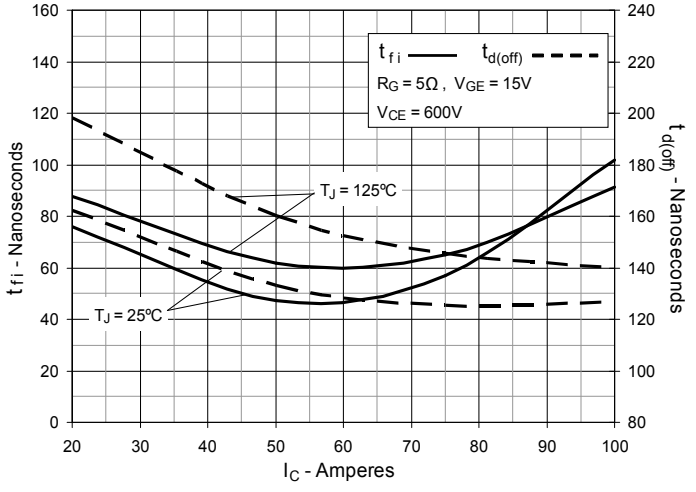


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

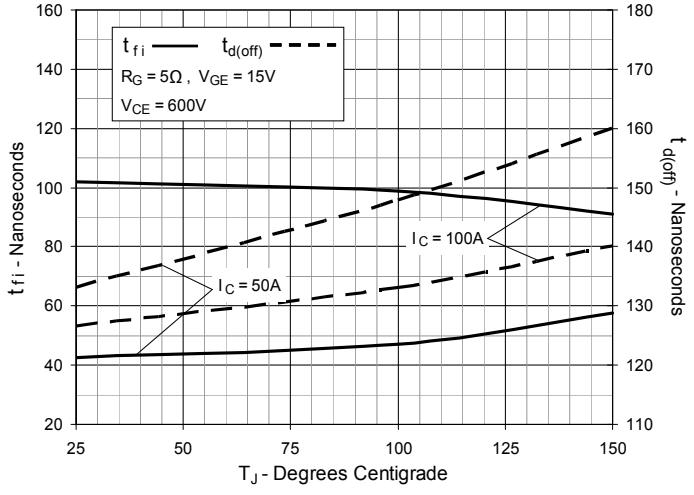


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

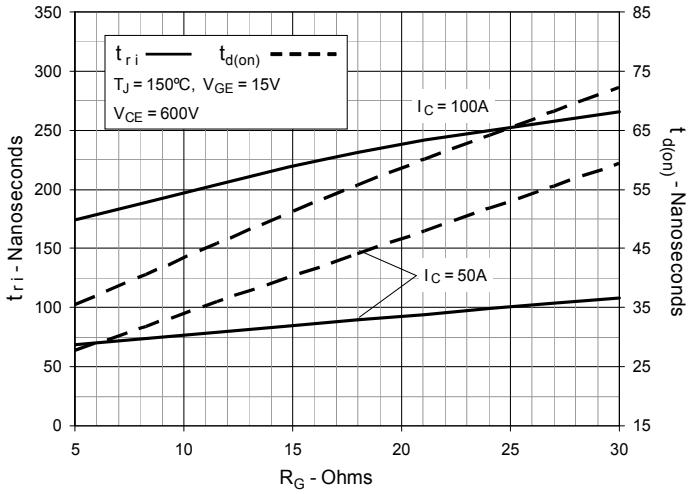


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

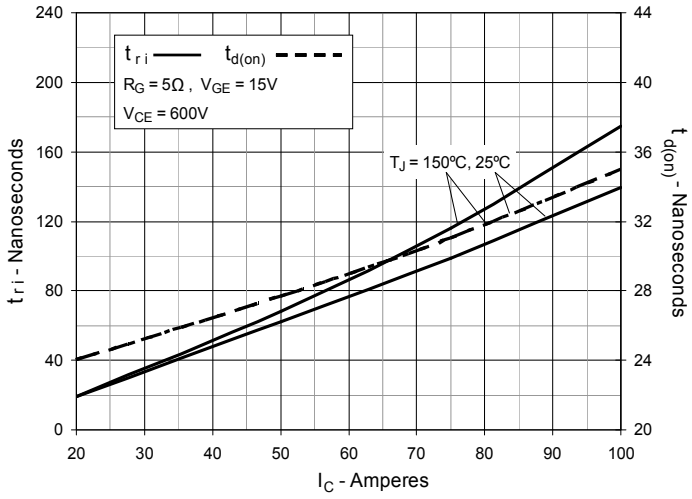


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature

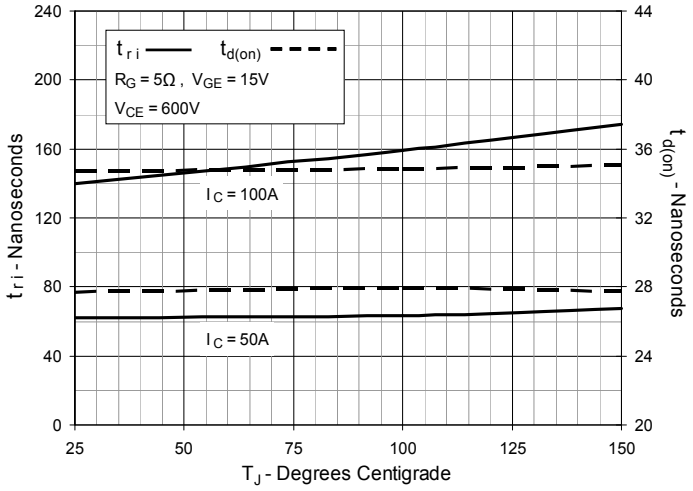


Fig. 21. Maximum Transient Thermal Impedance (Diode)

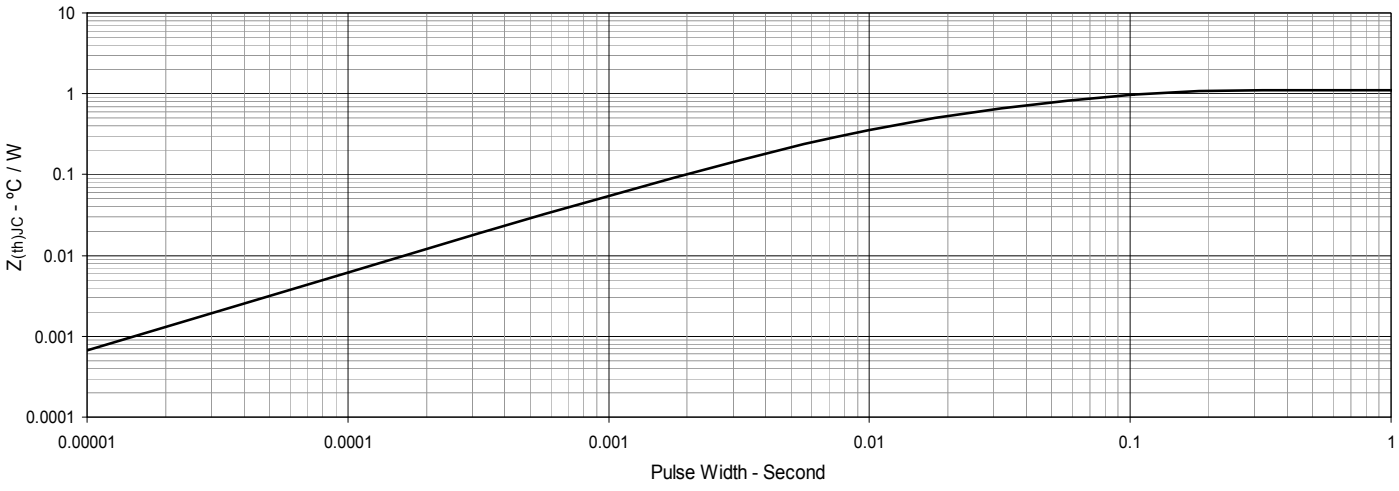


Fig. 22. Forward Current I_F vs V_F

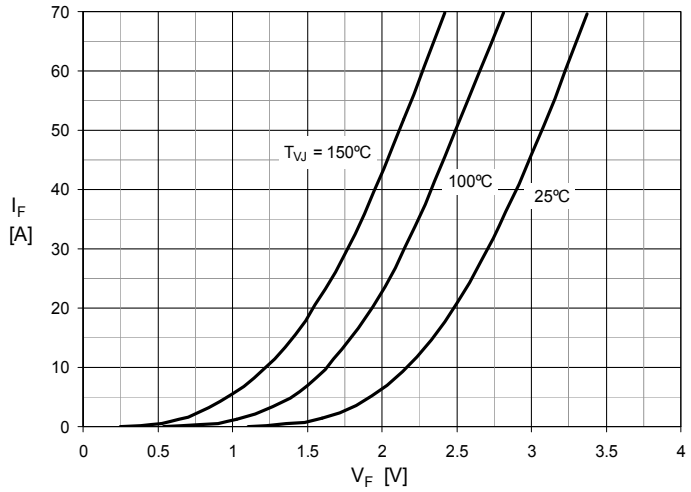


Fig. 23. Reverse Recovery Charge Q_{RM} vs. -di_F/dt

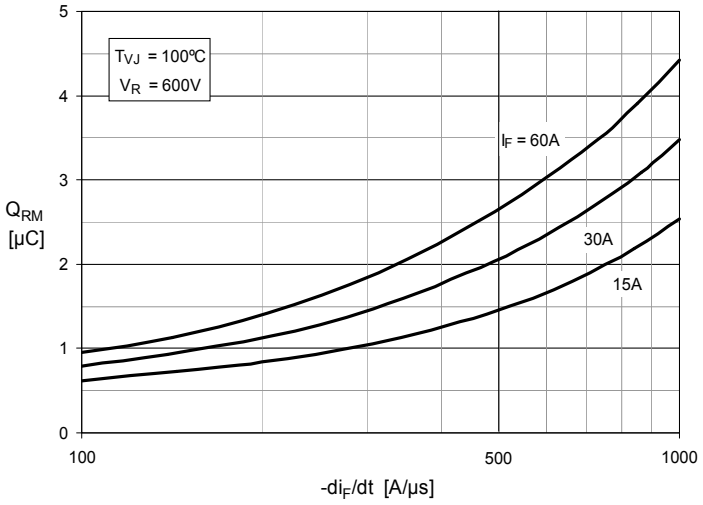


Fig. 24. Peak Reverse Current I_{RM} vs. -di_F/dt

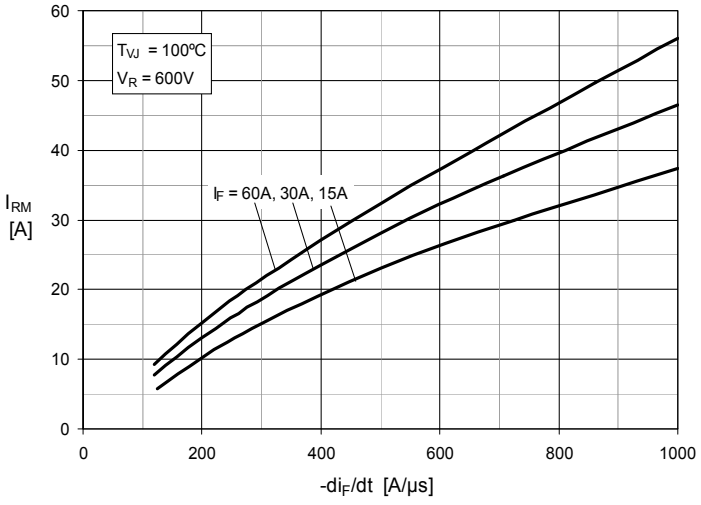


Fig. 25. Dynamic Parameters Q_{RM}, I_{RM} vs. T_{VJ}

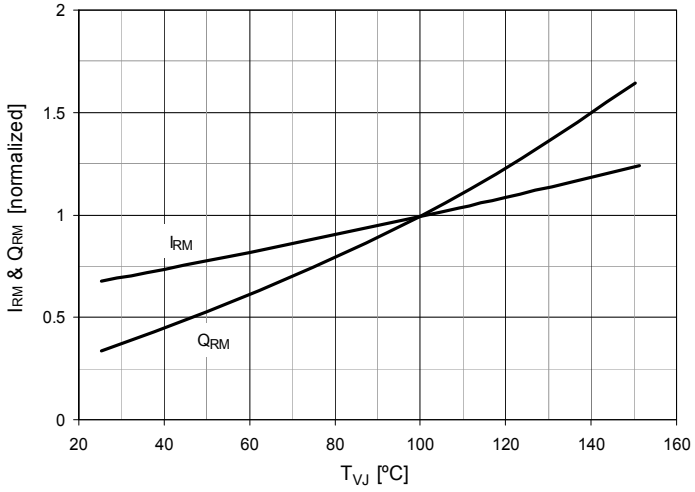


Fig. 26. Recovery Time t_{rr} vs. -di_F/dt

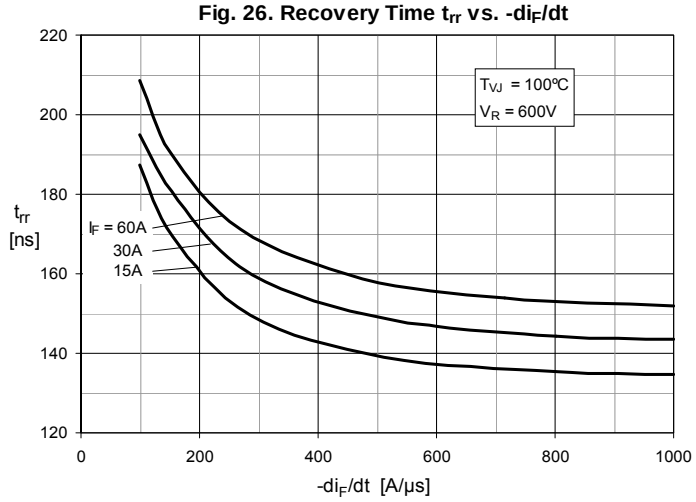


Fig. 27. Peak Forward Voltage V_{FR}, t_{rr} vs -di_F/dt